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INFO	RMATION I	DISC	LOSURE	Application Number	10/659585
STATEMENT BY APPLICANT				Filing Date	September 1€, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
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				Examiner Name	Heather Doty
Sheet	2	of	2	Attorney Docket Number	0756-7196

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Examiner Signature Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.